

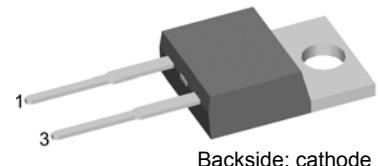
Schottky

High Performance Schottky Diode
Low Loss and Soft Recovery
Single Diode

V_{RRM} = 45 V
I_{FAV} = 15 A
V_F = 0.63 V

Part number

DSA 15 I 45PA



Backside: cathode

Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm}-values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package:

- TO-220AC
- Industry standard outline
 - Epoxy meets UL 94V-0
 - RoHS compliant

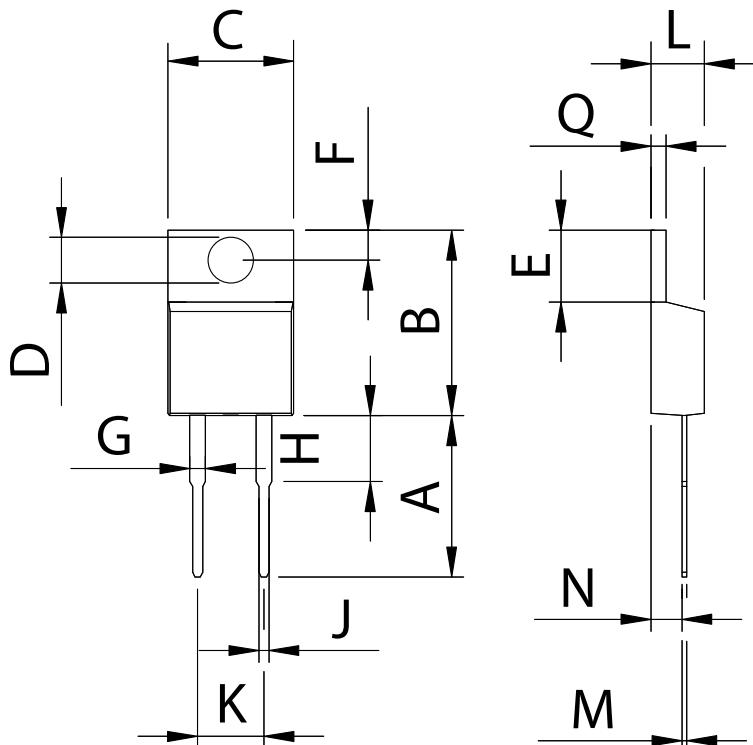
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse voltage	T _{vj} = 25 °C			45	V
I _R	reverse current	V _R = 45 V	T _{vj} = 25 °C		0.3	mA
		V _R = 45 V	T _{vj} = 125 °C		2.5	mA
V _F	forward voltage	I _F = 15 A	T _{vj} = 25 °C		0.75	V
		I _F = 30 A			0.91	V
		I _F = 15 A	T _{vj} = 125 °C		0.63	V
		I _F = 30 A			0.79	V
I _{FAV}	average forward current	rectangular, d = 0.5	T _c = 155 °C		15	A
V _{F0} r _F	threshold voltage slope resistance } for power loss calculation only		T _{vj} = 175 °C		0.42	V
					9.9	mΩ
R _{thJC}	thermal resistance junction to case				1.75	K/W
T _{vj}	virtual junction temperature		-55		175	°C
P _{tot}	total power dissipation	T _c = 25 °C			85	W
I _{FSM}	max. forward surge current	t _p = 10 ms (50 Hz), sine	T _{vj} = 45 °C		140	A
C _J	junction capacitance	V _R = tbd V; f = 1 MHz	T _{vj} = 25 °C		tbd	pF
E _{AS}	non-repetitive avalanche energy	I _{AS} = tbd A; L = 100 μH	T _{vj} = 25 °C		tbd	mJ
I _{AR}	repetitive avalanche current	V _A = 1.5 · V _R typ.; f = 10 kHz			tbd	A

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per pin*			35	A
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N
T_{stg}	storage temperature		-55		150	°C
Weight				2		g

* I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-220AC



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	14.73	0.500	0.580
B	14.23	16.51	0.560	0.650
C	9.66	10.66	0.380	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.2300	0.420
F	2.54	3.42	0.100	0.135
G	1.15	1.77	0.045	0.070
H	-	6.35	-	0.250
J	0.64	0.89	0.025	0.035
K	4.83	5.33	0.190	0.210
L	3.56	4.82	0.140	0.190
M	0.51	0.76	0.020	0.030
N	2.04	2.49	0.080	0.115
Q	0.64	1.39	0.025	0.055